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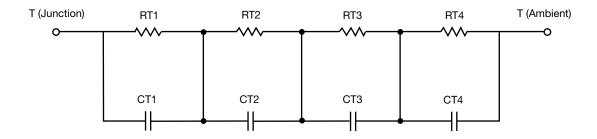
# **R-C Thermal Model Parameters**

### **DESCRIPTION**

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in PSpice, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the PSpice simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the PSpice Platform".

#### **R-C THERMAL MODEL FOR TANK CONFIGURATION**



R-C VALUES FOR TANK CONFIGURATION  THERMAL RESISTANCE (°C/W)					
RT1	n/a	654.4054m	n/a		
RT2	n/a	418.3270m	n/a		
RT3	n/a	121.6249m	n/a		
RT4	n/a	405.6427m	n/a		
	THERMAL CAPAC	ITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CT1	n/a	1.6648m	n/a		
CT2	n/a	60.2889m	n/a		
CT3	n/a	32.1508m	n/a		
CT4	n/a	361.4425m	n/a		

#### Note

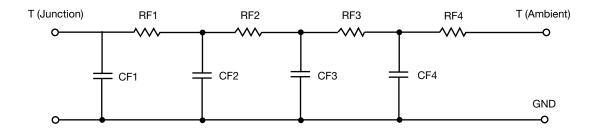
n/a indicates not applicable

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

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## **R-C THERMAL MODEL FOR FILTER CONFIGURATION**



-C VALUES FOR FILTER CONFIGURATION  THERMAL RESISTANCE (°C/W)					
RF1	n/a	422.9873m	n/a		
RF2	n/a	357.1151m	n/a		
RF3	n/a	502.6891m	n/a		
RF4	n/a	317.2085m	n/a		
	THERMAL CAPAC	ITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CF1	n/a	1.5283m	n/a		
CF2	n/a	46.4073u	n/a		
CF3	n/a	42.0438m	n/a		
CF4	n/a	360.7781m	n/a		

#### Note

• n/a indicates not applicable





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